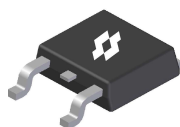


Product Summary

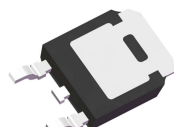
V_{DS}	$R_{DS(ON_TYP)}$	I_{D_MAX}
100 V	112 m Ω @ $V_{GS} = 10V$	7.4 A
	139 m Ω @ $V_{GS} = 4.5V$	

Features

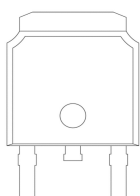
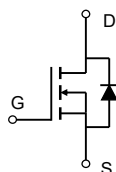
- Low On-Resistance
- Excellent FoM (figure of merit)
- 100% ΔV_{DS} & UIS & Rg Tested

TO252-3L


Top View



Bottom View


PIN Configuration
(Top View)


Schematic Diagram


Applications

- Load/Signal Switches
- DC/DC in Telecoms and Industrial
- High frequency switching, synchronous rectification

Mechanical Data

- Green Molding Compound
- Moisture Sensitivity: Level 3 per J-STD-020
- UL Flammability Classification Rating 94V-0

Ordering Information

Orderable Part Number	Package Type	Device Marking	Form	Quantity (pcs)
SMT10T130ALU	TO252-3L	10T130AL	13" Tape&Reel	2,500

Maximum Ratings (@ $T_C = 25^\circ\text{C}$, unless otherwise specified.)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	100	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS} = 10V$) ⁽¹⁾	I_D	7.4	A
		4.7	A
Pulsed Drain Current ⁽²⁾	I_{DM}	30	A
Single Pulse Avalanche Energy ⁽³⁾	E_{AS}	1.6	mJ
Single Pulse Avalanche Current ($L = 0.1mH$)	I_{AS}	3.0	A
Power Dissipation	P_D	14	W
		5.6	W
Junction & Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient ⁽⁴⁾	$R_{\theta JA}$	55	70	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case ⁽⁵⁾	$R_{\theta JC}$	6.9	8.9	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$, unless otherwise specified.)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics ⁽⁶⁾						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V	-	-	1.0	μA
		T _J = 125°C	-	-	100	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics ⁽⁶⁾						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	1.2	1.8	2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 2.0A	-	112	137	mΩ
		V _{GS} = 4.5V, I _D = 1.0A	-	139	175	mΩ
Forward Transconductance	g _{fs}	V _{DS} = 5.0V, I _D = 2.0A	-	4.9	-	S
Diodes Forward Voltage	V _{SD}	I _S = 2.0A, V _{GS} = 0V	-	0.9	1.2	V
Dynamic Characteristics ⁽⁷⁾						
Input Capacitance	C _{iss}	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz	-	79	-	pF
Output Capacitance	C _{oss}		-	40	-	pF
Reverse Transfer Capacitance	C _{rss}		-	2.4	-	pF
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	-	2.1	-	Ω
Switching Characteristics ⁽⁷⁾						
Turn-On DelayTime	t _{d(on)}	V _{GS} = 10V, V _{DS} = 50V I _D = 2.0A, R _{GEN} = 3.0Ω	-	1.2	-	ns
Rise Time	t _r		-	2.0	-	ns
Turn-Off DelayTime	t _{d(off)}		-	5.2	-	ns
Fall Time	t _f		-	2.0	-	ns
Gate Charge Characteristics ⁽⁷⁾						
Total Gate Charge (V _{GS} = 10V)	Q _g	V _{DS} = 50V, I _D = 2.0A V _{GS} = 10V	-	2.2	-	nC
Total Gate Charge (V _{GS} = 4.5V)	Q _g		-	1.2	-	nC
Gate-Source Charge	Q _{gs}		-	0.27	-	nC
Gate-Drain Charge	Q _{gd}		-	0.57	-	nC
Gate Plateau Voltage	V _{plateau}		-	2.8	-	V
Drain-Source Diode Characteristics ⁽⁷⁾						
Body Diode Reverse Recovery Time	t _{rr}	I _F = 2.0A, dI/dt = 100A/μs,	-	11	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	T _J = 25°C	-	25	-	nC
Diode Forward Current	I _S	T _C = 25°C	-	-	7	A

Notes:

1. This current is chip limited, which is calculated based on R_{thjc} .
2. This current is calculated on single pulse with 10 μs Single Pulse.
3. Defined by design, not subject to production test, E_{AS} condition: $T_J = 25^\circ\text{C}$, $V_{DD} = 50V$, $V_{GS} = 10V$, $L = 1.0mH$.
4. Device mounted on FR-4 substrate PC board with 2oz copper in 1inch square cooling area.
5. Thermal resistance from junction to the exposed pad.
6. Short duration pulse test used to minimize self-heating effect.
7. Defined by design, not subject to production.

Typical Electrical and Thermal Characteristics

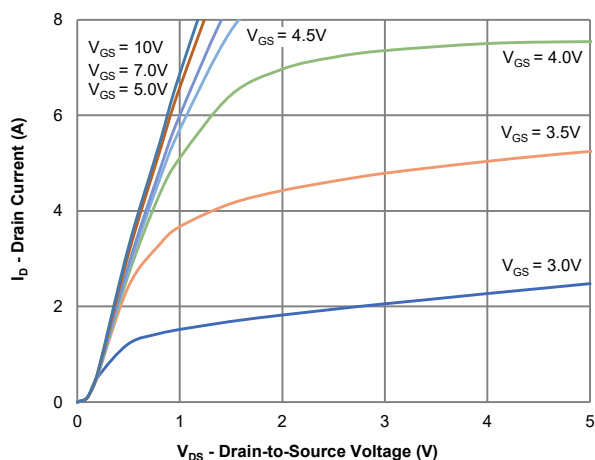


Figure 1: Output Characteristics

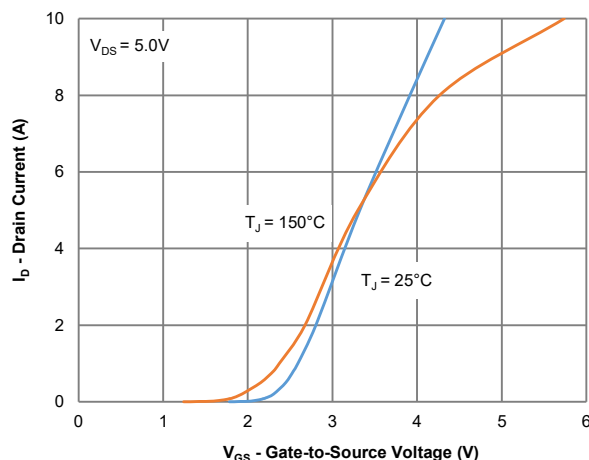


Figure 2: Transfer Characteristics

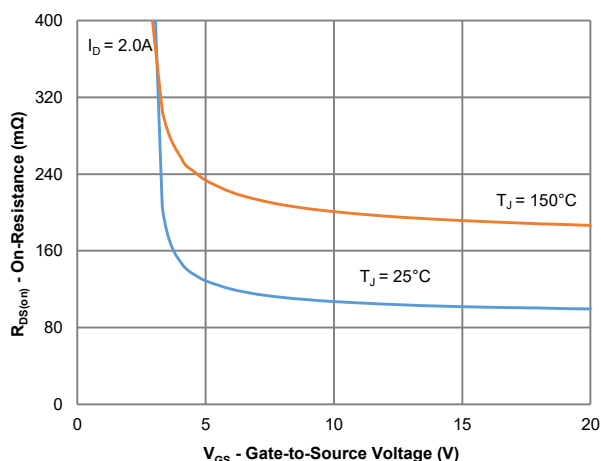


Figure 3: On-Resistance vs. Gate-Source Voltage

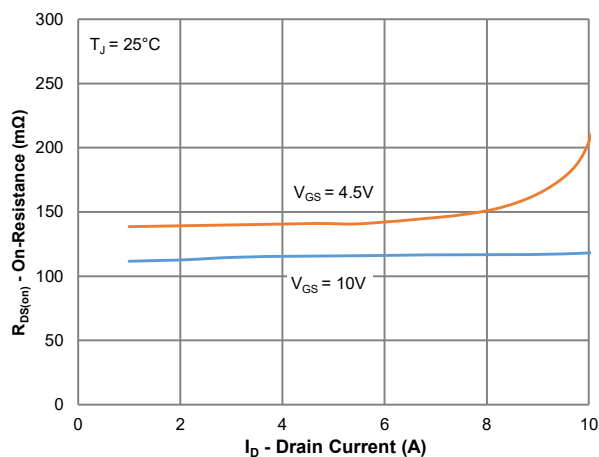


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

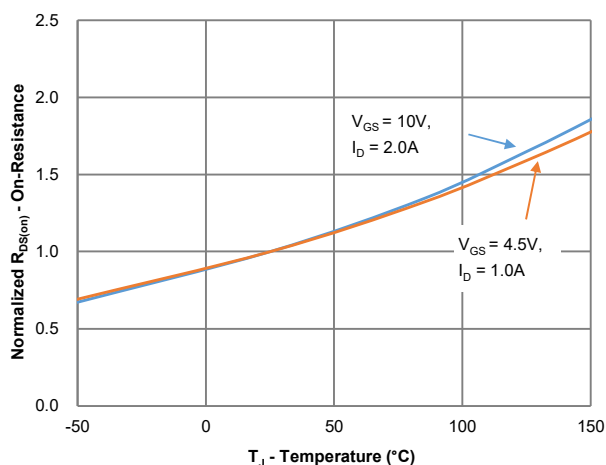


Figure 5: On-Resistance vs. Junction Temperature

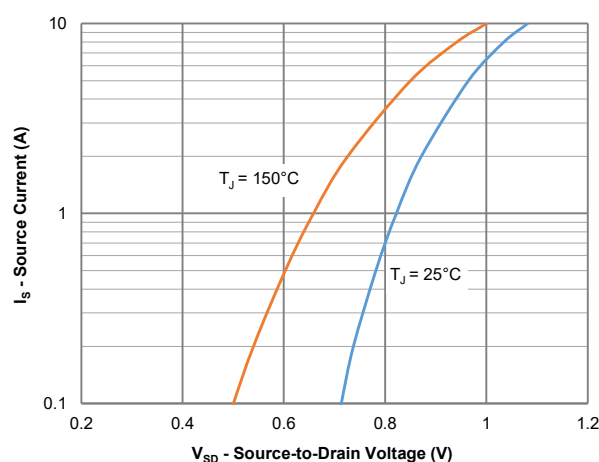
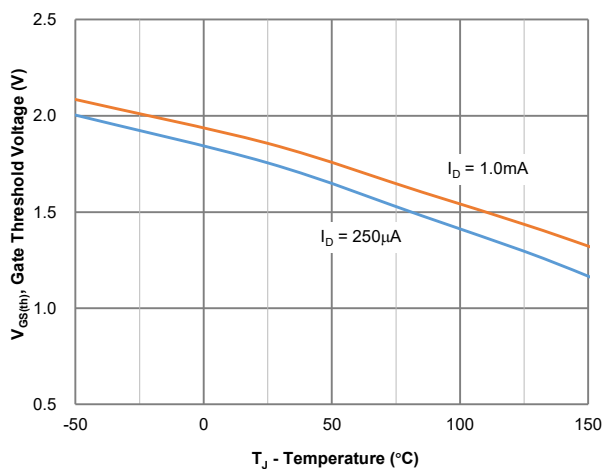
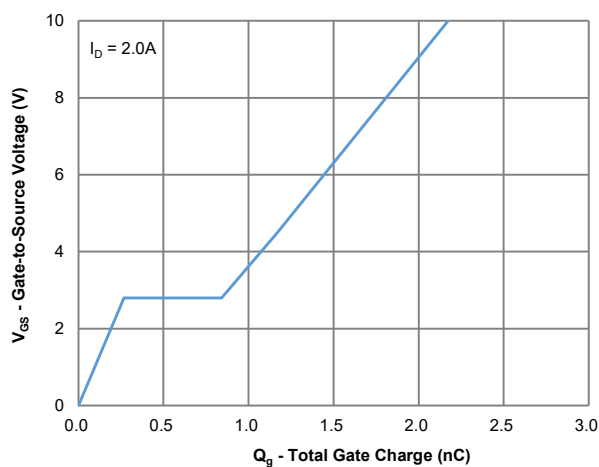
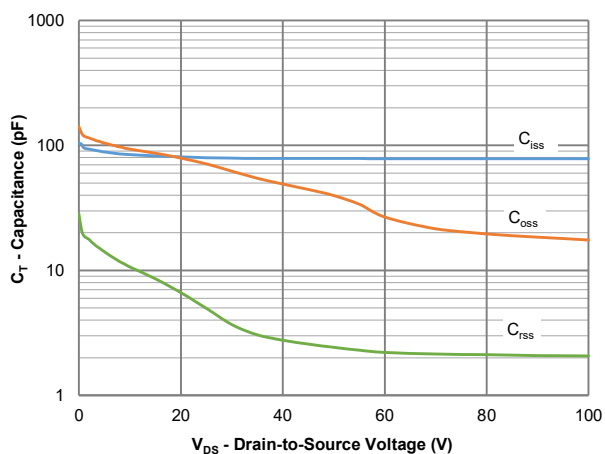
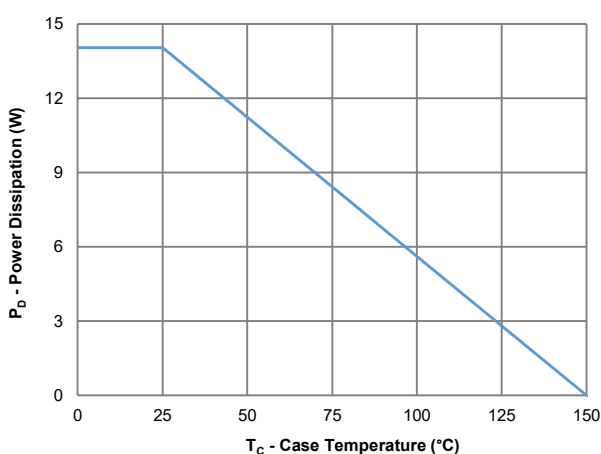
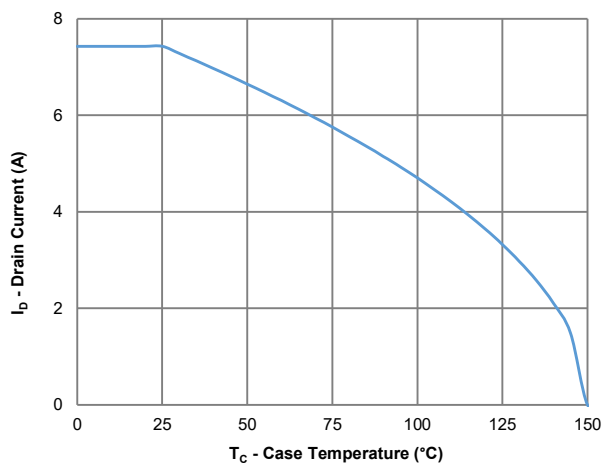
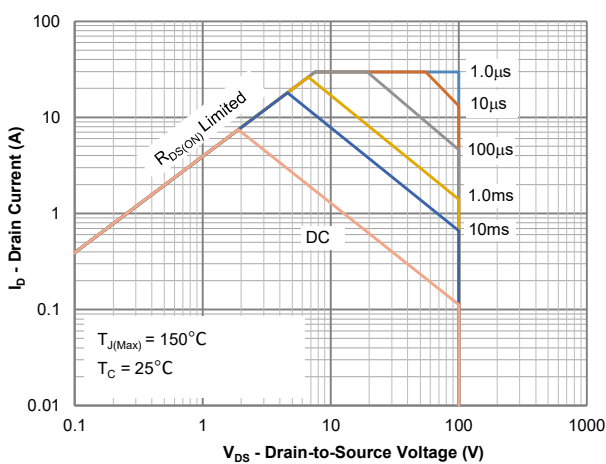


Figure 6: Source-Drain Diode Forward Voltage

Typical Electrical and Thermal Characteristics

Figure 7: Gate Threshold Variation vs. Junction Temperature

Figure 8: Gate Charge Characteristics

Figure 9: Capacitance Characteristics

Figure 10: Power Derating

Figure 11: Current Derating

Figure 12: Safe Operating Area

Typical Electrical and Thermal Characteristics

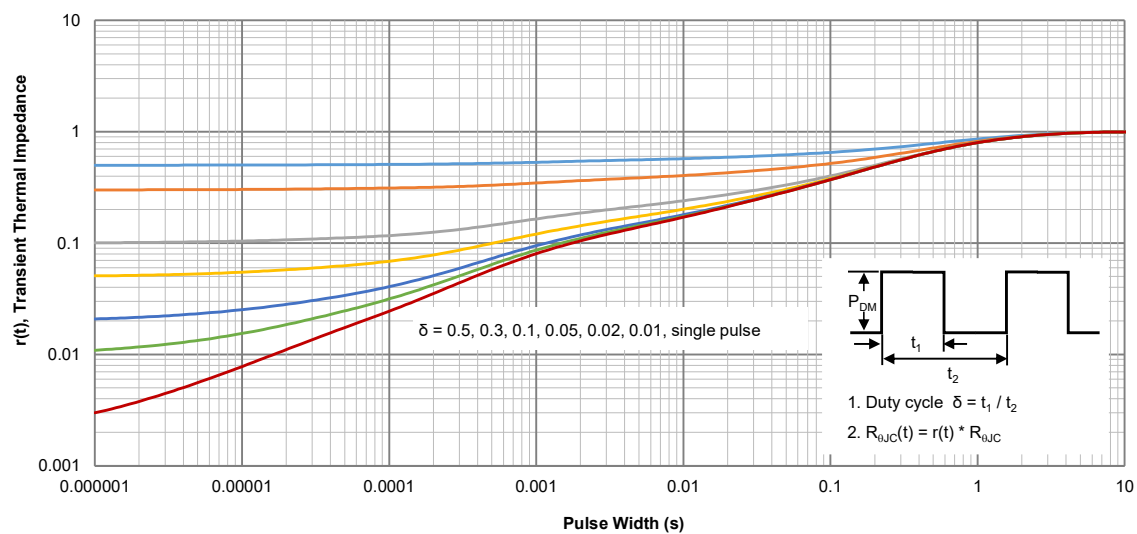
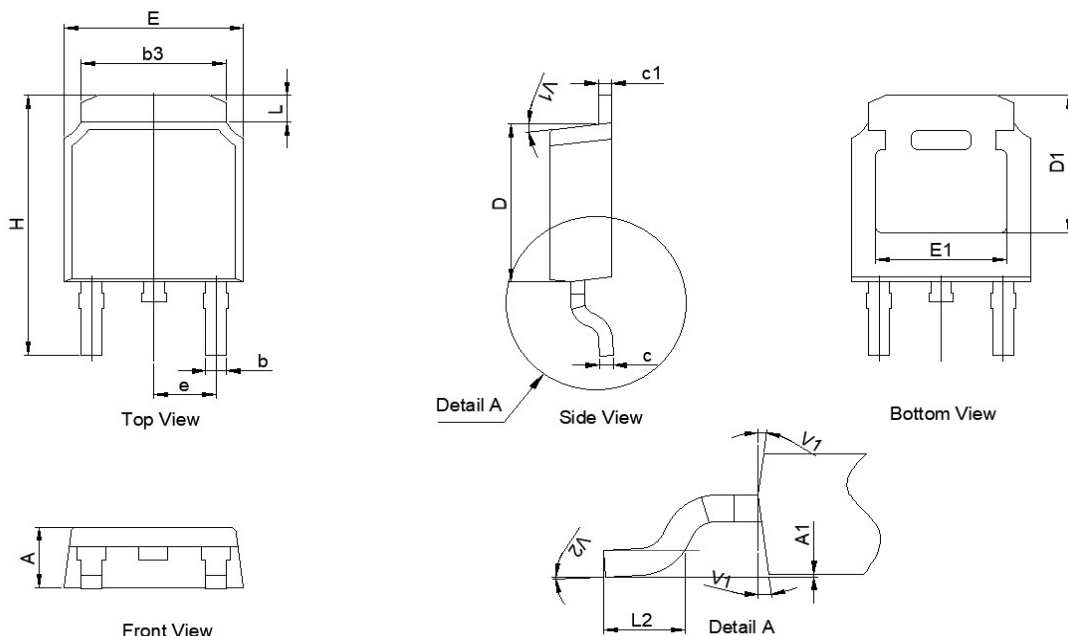


Figure 13: Normalized Maximum Transient Thermal Impedance

TO252-3L Package Outline
Package Outline

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	0	-	0.13
b	0.62	0.76	0.90
c	0.40	0.50	0.61
c1	0.46	0.50	0.58
D	5.90	6.10	6.30
D1	5.05	--	--
E	6.35	6.60	6.80
E1	4.32	--	--
b3	5.21	5.38	5.55
e	2.29 BSC		
H	9.40	10.00	10.40
L	0.89	--	1.27
L2	1.40		1.78
V1	7° REF		
V2	0°	-	6°

Recommend Soldering Footprint
